Abstracts

Low-Noise High-Power Heterojunction Bipolar Transistors for Mixed-Mode Applications

T. Jenkins, D. Barlage, J. Barrette, R. Lee, L. Liou, C. Bozada, R. Dettmer, R. Fitch, M. Mack and J. Sewell. "Low-Noise High-Power Heterojunction Bipolar Transistors for Mixed-Mode Applications." 1995 MTT-S International Microwave Symposium Digest 95.3 (1995 Vol. III [MWSYM]): 1129-1132.

A novel heterojunction bipolar transistor (HBT), which provides state-of-the-art noise and record power density through X-band, was developed. This performance is due to advanced design and fabrication techniques. This HBT is readily transferable to mixed-mode applications, such as portable telephones and radar transmit/receive modules.

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